

N-Channel Enhancement Mode Power MOSFET

Description

The RM35N30DF uses advanced trench technology and design to provide excellent $R_{DS(ON)}$ with low gate charge. It can be used in a wide variety of applications.

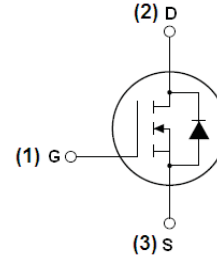
General Features

- $V_{DS} = 30V, I_D = 35A$
 $R_{DS(ON)} < 7.0m\Omega @ V_{GS}=10V$
 $R_{DS(ON)} < 12m\Omega @ V_{GS}=4.5V$
- High density cell design for ultra low $R_{DS(on)}$
- Fully characterized avalanche voltage and current
- Good stability and uniformity with high E_{AS}
- Excellent package for good heat dissipation
- Special process technology for high ESD capability

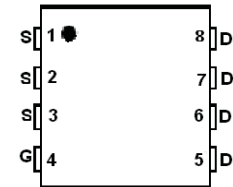
Application

- Secondary side synchronous rectifier
- High side switch in POL DC/DC converter
- P/N suffix V means AEC-Q101 qualified, e.g:RM35N30DFV
- Halogen-free

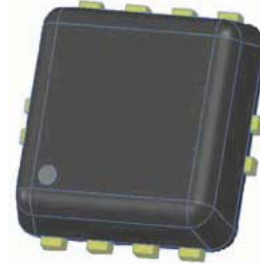
100% UIS TESTED!



Schematic diagram



Marking and pin assignment



DFN 5x6 EP top view

Package Marking and Ordering Information

Device Marking	Device	Device Package	Reel Size	Tape width	Quantity
35N30	RM35N30DF	DFN 5x6 EP	-	-	-

Absolute Maximum Ratings ($T_C=25^{\circ}C$ unless otherwise noted)

Parameter	Symbol	Limit	Unit
Drain-Source Voltage	V_{DS}	30	V
Gate-Source Voltage	V_{GS}	± 20	V
Drain Current-Continuous	I_D	35	A
Pulsed Drain Current	I_{DM}	120	A
Maximum Power Dissipation	P_D	40	W
Derating factor		0.32	W/ $^{\circ}C$
Single pulse avalanche energy ^(Note 5)	E_{AS}	150	mJ
Operating Junction and Storage Temperature Range	T_J, T_{STG}	-55 To 150	$^{\circ}C$

Thermal Characteristic

Thermal Resistance, Junction-to-Case ^(Note 2)	$R_{\theta JC}$	3.1	°C/W
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Electrical Characteristics (TC=25°C unless otherwise noted)

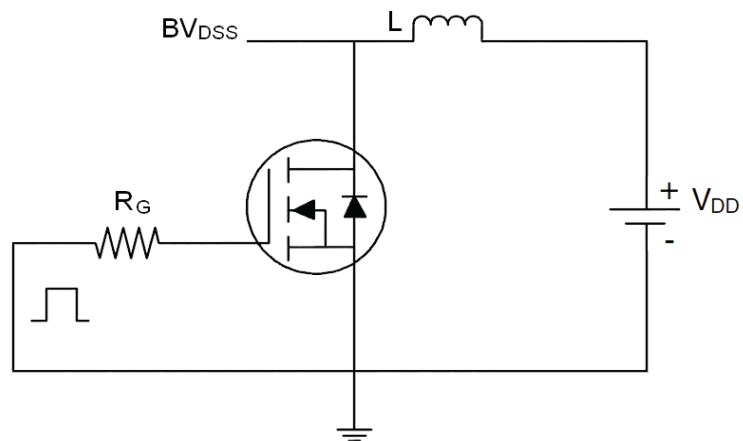
Parameter	Symbol	Condition	Min	Typ	Max	Unit
Off Characteristics						
Drain-Source Breakdown Voltage	BV _{DSS}	V _{GS} =0V I _D =250μA	30	33	-	V
Zero Gate Voltage Drain Current	I _{DSS}	V _{DS} =30V, V _{GS} =0V	-	-	1	μA
Gate-Body Leakage Current	I _{GSS}	V _{GS} =±20V, V _{DS} =0V	-	-	±100	nA
On Characteristics ^(Note 3)						
Gate Threshold Voltage	V _{GS(th)}	V _{DS} =V _{GS} , I _D =250μA	1	1.6	3	V
Drain-Source On-State Resistance	R _{DS(ON)}	V _{GS} =10V, I _D =12A	-	5.9	7.0	mΩ
		V _{GS} =4.5V, I _D =10A	-	8.9	12.0	
Forward Transconductance	g _{FS}	V _{DS} =10V, I _D =12A	30	-	-	S
Dynamic Characteristics ^(Note4)						
Input Capacitance	C _{iss}	V _{DS} =15V, V _{GS} =0V, F=1.0MHz	-	2330	-	PF
Output Capacitance	C _{oss}		-	460	-	PF
Reverse Transfer Capacitance	C _{rss}		-	230	-	PF
Switching Characteristics ^(Note 4)						
Turn-on Delay Time	t _{d(on)}	V _{DD} =15V, I _D =12A V _{GS} =10V, R _{GEN} =6Ω	-	18	-	nS
Turn-on Rise Time	t _r		-	10	-	nS
Turn-Off Delay Time	t _{d(off)}		-	34	-	nS
Turn-Off Fall Time	t _f		-	10	-	nS
Total Gate Charge	Q _g	V _{DS} =15V, I _D =12A, V _{GS} =10V	-	45	-	nC
Gate-Source Charge	Q _{gs}		-	13	-	nC
Gate-Drain Charge	Q _{gd}		-	10	-	nC
Drain-Source Diode Characteristics						
Diode Forward Voltage ^(Note 3)	V _{SD}	V _{GS} =0V, I _S =12A	-	0.85	1.2	V
Diode Forward Current ^(Note 2)	I _S		-	-	35	A
Reverse Recovery Time	t _{rr}	T _J = 25°C, I _F = 12A di/dt = 100A/μs(Note3)	-	-	47	nS
Reverse Recovery Charge	Q _{rr}		-	-	25	nC
Forward Turn-On Time	t _{on}	Intrinsic turn-on time is negligible (turn-on is dominated by LS+LD)				

Notes:

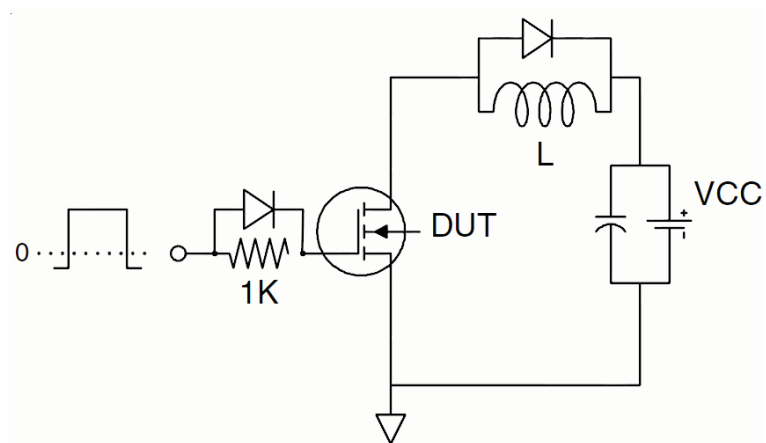
1. Repetitive Rating: Pulse width limited by maximum junction temperature.
2. Surface Mounted on FR4 Board, $t \leq 10$ sec.
3. Pulse Test: Pulse Width $\leq 300\mu s$, Duty Cycle $\leq 2\%$.
4. Guaranteed by design, not subject to production
5. EAS condition: $T_J=25^\circ C, V_{DD}=15V, V_G=10V, L=0.1mH, R_g=25\Omega$

Test Circuit

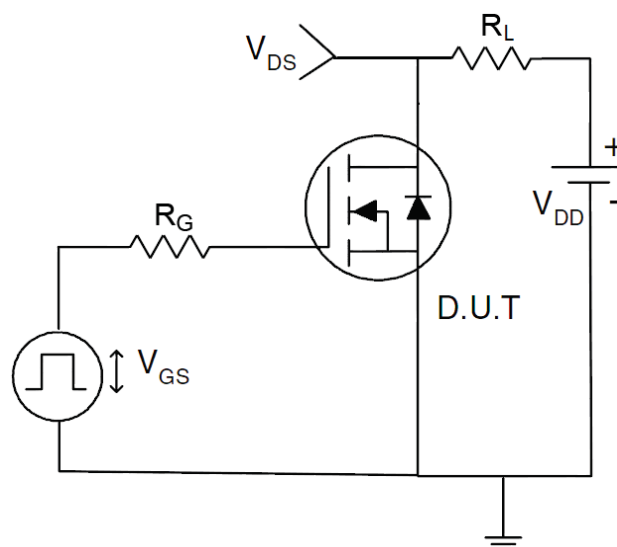
1) E_{AS} Test Circuits



2) Gate Charge Test Circuit



3) Switch Time Test Circuit



RATING AND CHARACTERISTICS CURVES (RM35N30DF)

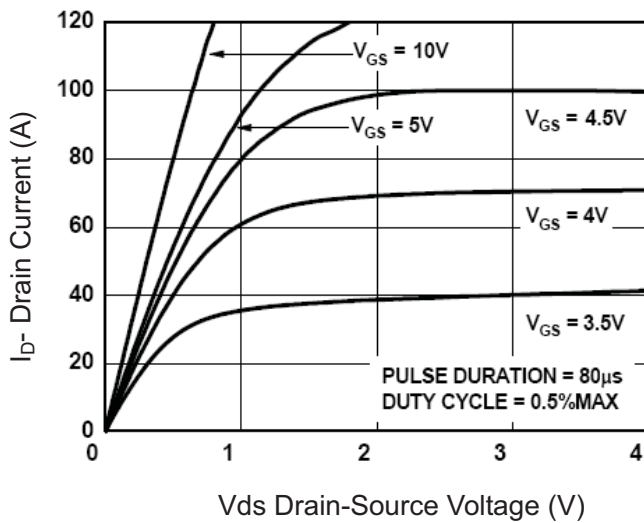


Figure 1 Output Characteristics

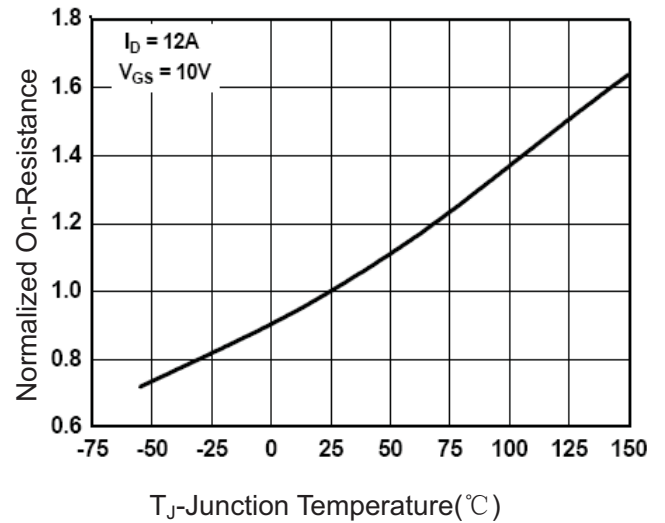


Figure 4 Rdson-Junction Temperature

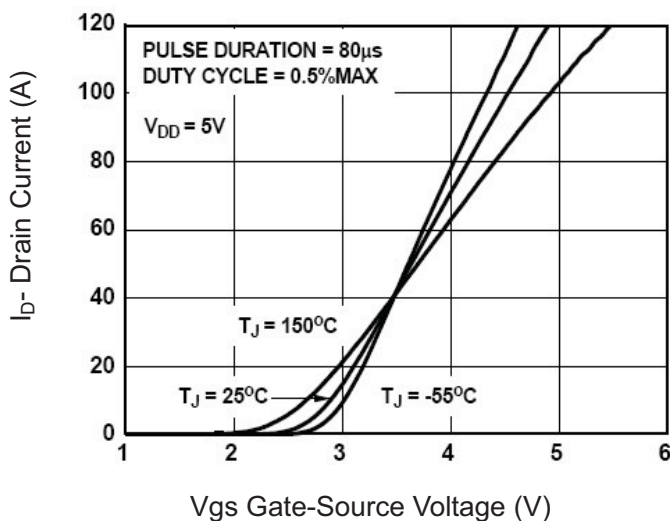


Figure 2 Transfer Characteristics

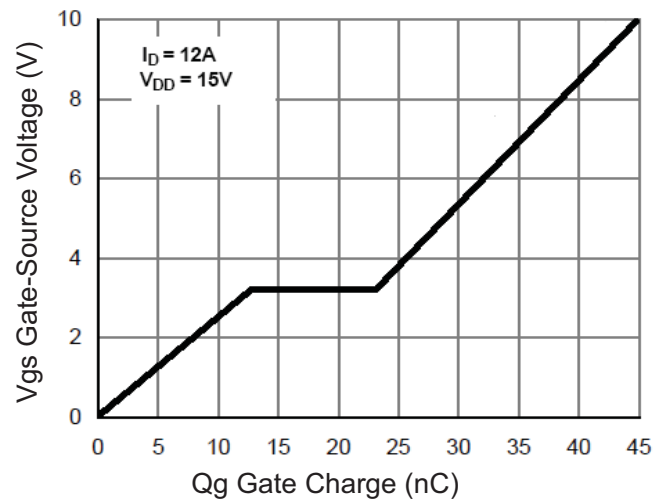


Figure 5 Gate Charge

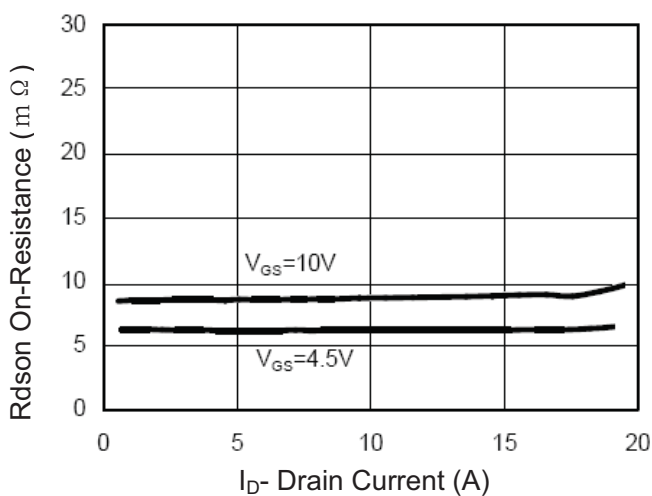


Figure 3 Rdson- Drain Current

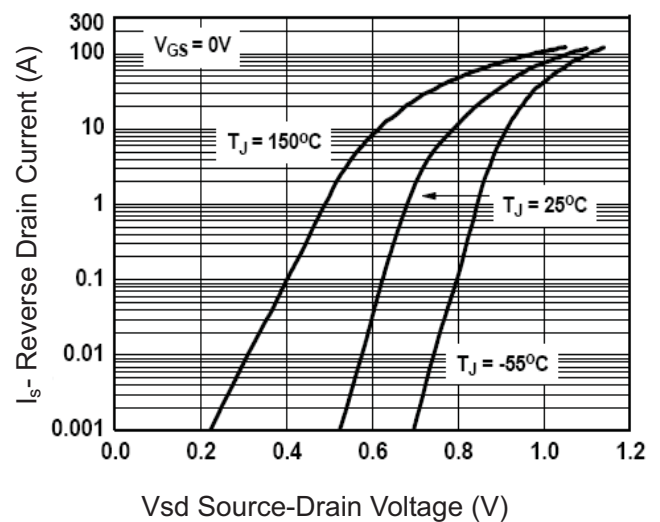


Figure 6 Source- Drain Diode Forward

RATING AND CHARACTERISTICS CURVES (RM35N30DF)

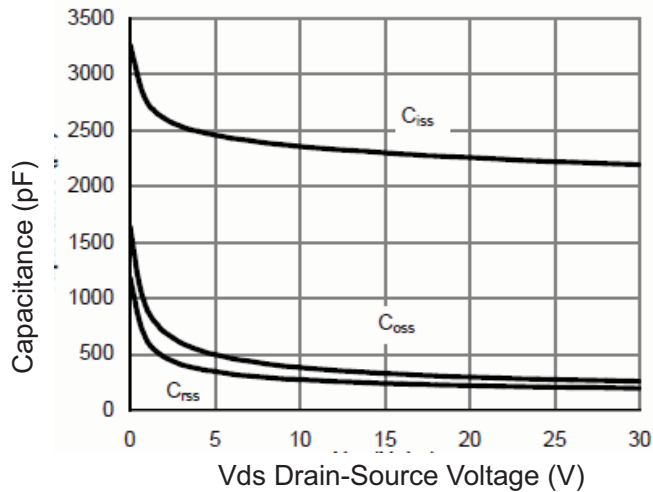


Figure 7 Capacitance vs Vds

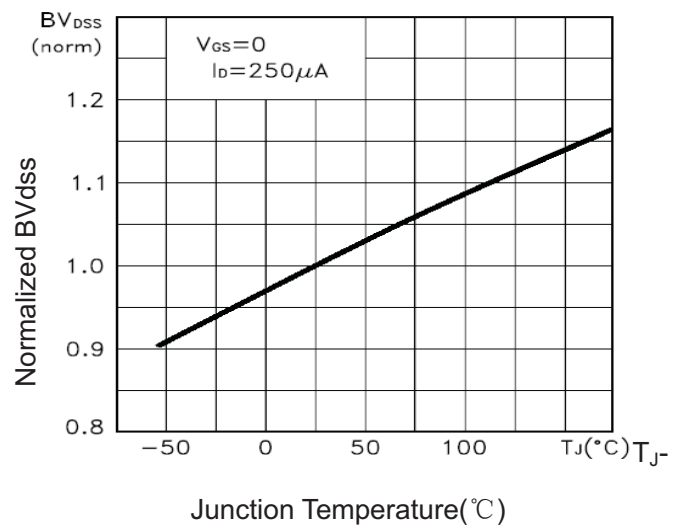


Figure 9 BV_{DSS} vs Junction Temperature

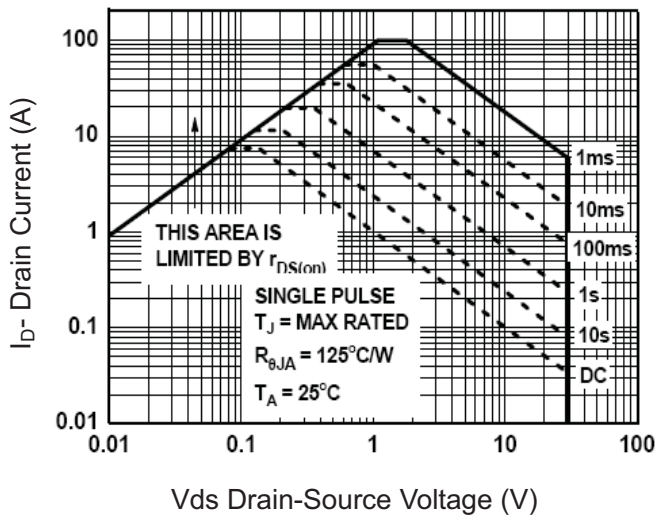


Figure 8 Safe Operation Area

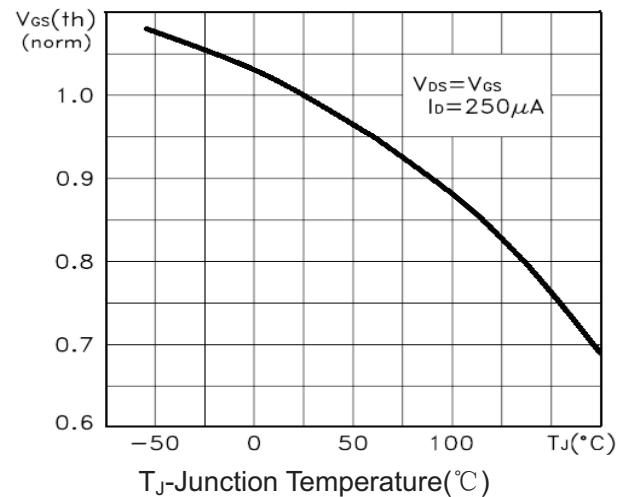


Figure 10 $V_{GS(th)}$ vs Junction Temperature

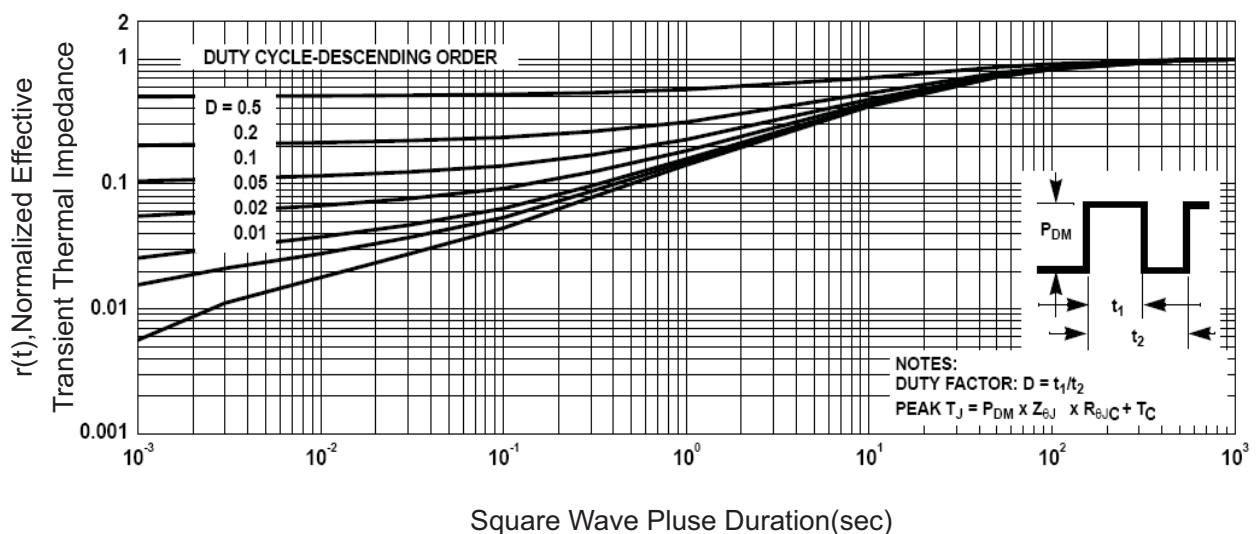
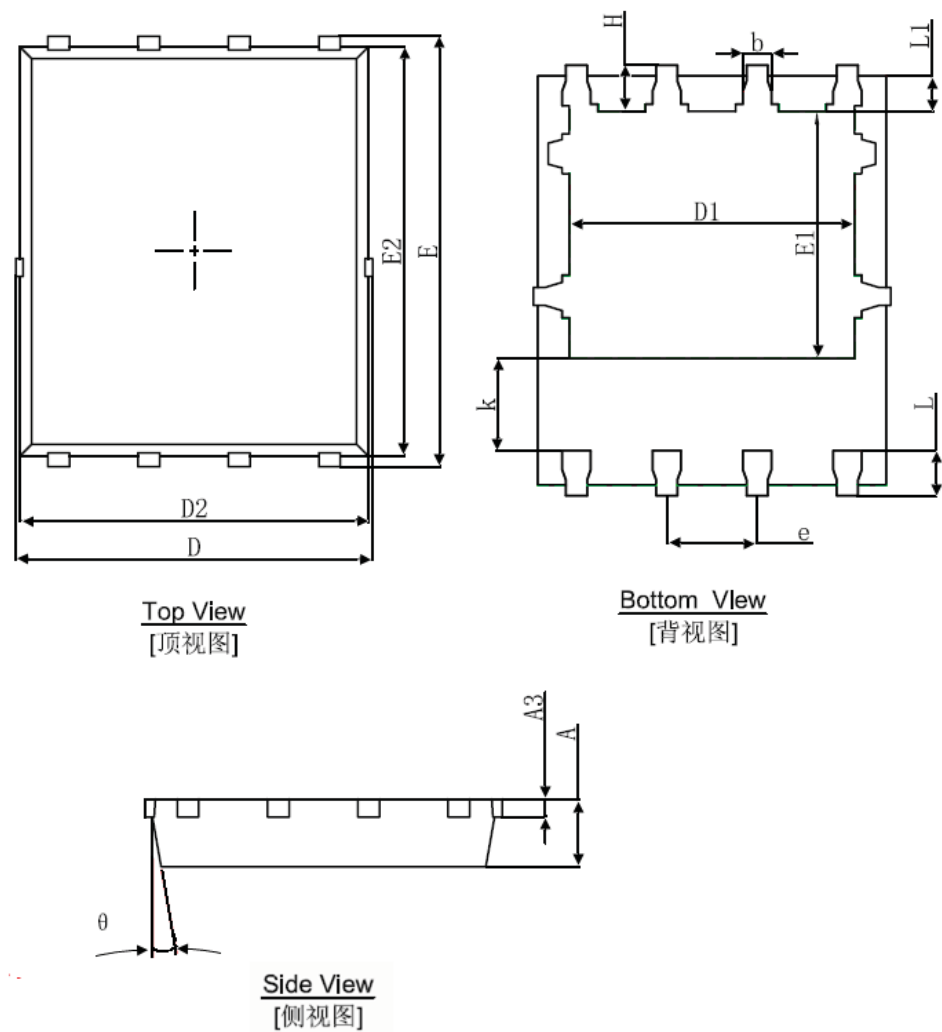


Figure 11 Normalized Maximum Transient Thermal Impedance

DFN5X6-8L Package Information



Symbol	Dimensions In Millimeters		Dimensions In Inches	
	Min.	Max.	Min.	Max.
A	0.900	1.000	0.035	0.039
A3	0.254REF.		0.010REF.	
D	4.944	5.096	0.195	0.201
E	5.974	6.126	0.235	0.241
D1	3.910	4.110	0.154	0.162
E1	3.375	3.575	0.133	0.141
D2	4.824	4.976	0.190	0.196
E2	5.674	5.826	0.223	0.229
k	1.190	1.390	0.047	0.055
b	0.350	0.450	0.014	0.018
e	1.270TYP.		0.050TYP.	
L	0.559	0.711	0.022	0.028
L1	0.424	0.576	0.017	0.023
H	0.574	0.726	0.023	0.029
θ	8°	12°	8°	12°



RECTRON

Marking on the body



← Rectron Logo

3 5 N 3 0 ← Part No.

Y Y W W

Year – Code

(Y:18-----2018
19-----2019.....)

Week – code
(WW:01~52)

Package	Tube (pcs/tube)	Tube (pcs/inner box)	Tube (pcs/cartoon)	Tape&Reel (pcs/reel)	Tape&Reel (pcs/inner box)	Tape&Reel (pcs/cartoon)
DFN	100	10,000	100,000	2,500	5,000	40,000
SOP-8	100	10,000	100,000	4,000	4,000	20,000
TSSOP-8	100	32,000	128,000	3,000	6,000	48,000
SOT-23-3L	——	——	——	3,000	30,000	120,000
SOT-23-6L	——	——	——	3,000	30,000	120,000
SOT-23(6R)	——	——	——	3,000	30,000	120,000
SOT-363	——	——	——	3,000	30,000	120,000
SOT-523	——	——	——	3,000	30,000	120,000
SOT223	——	——	——	2,500	2,500	20,000
TO-220	50	1,000	5,000	——	——	——
TO-220F	50	1,000	10,000	——	——	——
TO-247	30	300	1,200	——	——	——
TO-251	80	4,000	40,000	——	——	——
TO-251S(4R)	80	4,000	40,000	——	——	——
TO-252-2L(4R)	80	4,000	40,000	2,500	2,500	25,000
TO-263-2L	50	1,000	10,000	800	800	8,000
TO-3P	30	300	3,000	——	——	——
TO-92	——	——	——	1,000(袋装)	10,000	100,000

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